

Replacement Abstract of the Disclosure

Circuitry is provided to allow early switching of input signals from a first configuration directed to blow a first anti-fuse to a second configuration directed to blow a second anti-fuse, yet still allow complete blowing of the first anti-fuse. Such circuitry may be applied to methods of repairing a memory device after testing. Data concerning available repair cells may be stored in at least one on-chip redundancy register.